SOT23-6 P

- CHANNEL MOSFET in a SOT23 -6 Plastic Package.

V_{DS}=-60V; I_D=-3A

$R_{DS(on)1}$@-10V ≤ 100mΩ(Type.83mΩ)

$R_{DS(on)2}$@-4.5V ≤ 130mΩ(Type.100mΩ)

Parameter	Symbol	Rating	Unit
Drain–Source Voltage	V_{DSS}	-60	V
Gate–Body Leakage Voltage	V_{GSS}	±20	V
Drain Current – Continuous	I_D	-3	A
Pulsed Drain Current	I_{DM}	-16	A
Power Dissipation	P_D	1.4	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 150	
Maximum Junction-to-Ambient	R		

/ Electrical Characteristic Curve

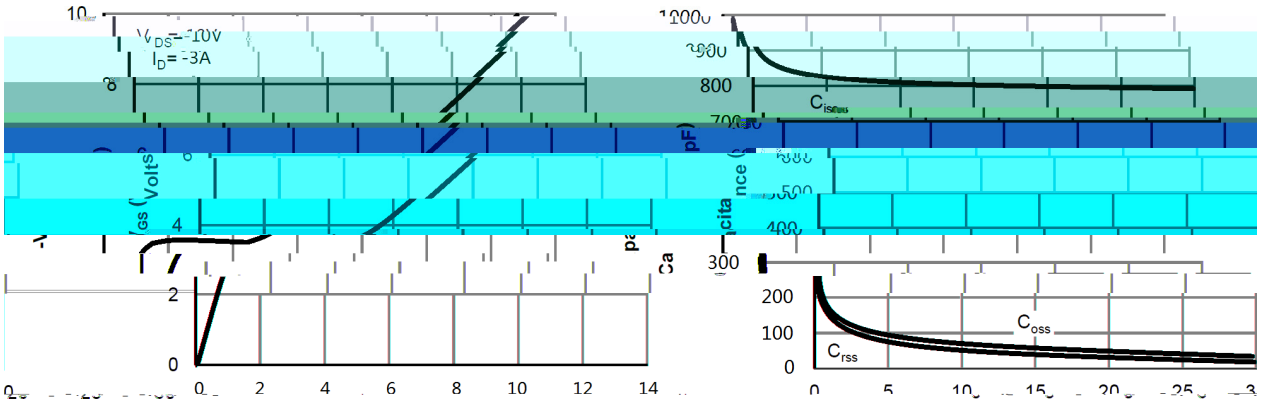
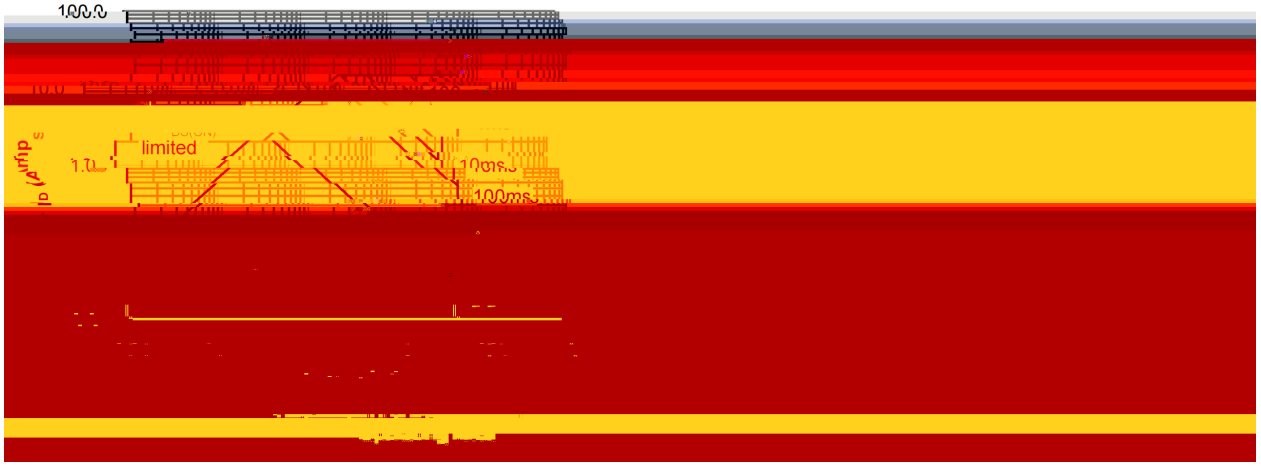
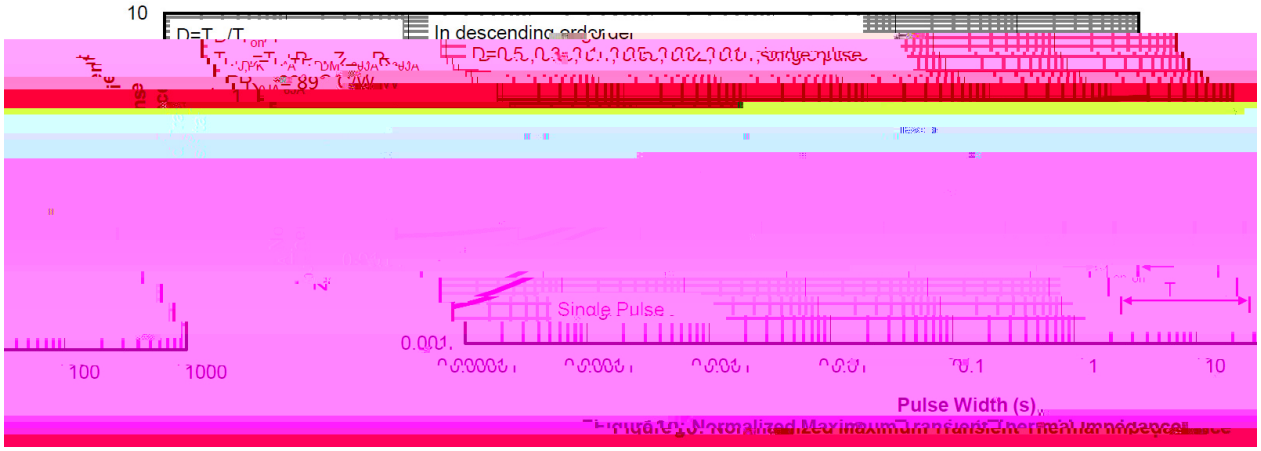


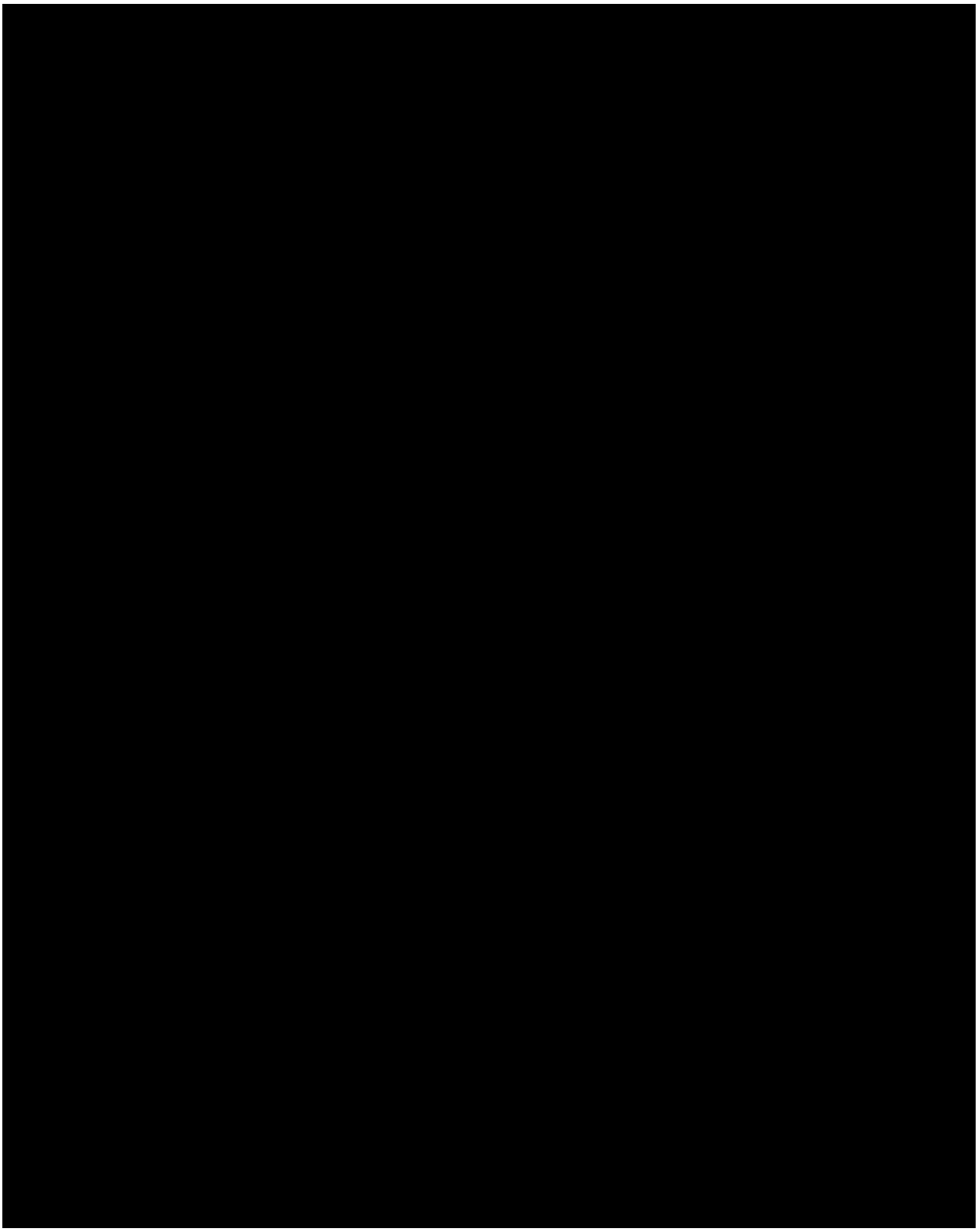
Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Cha

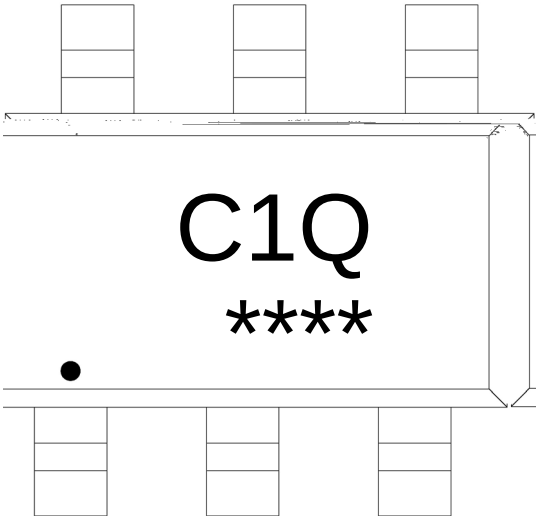




/ Package Dimensions



/ Marking Instructions



C1:

****:

Note:

Q:	Automobile halogen-free product Code
C1:	Product Type Code
****	Lot No. Code, code change with Lot No.

BRCS1C0P06MFQ

Rev.C Aug.-2025